

PMV48XPAR Datasheet



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DiGi Electronics Part Number PMV48XPAR-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMV48XPAR

Description MOSFET P-CH 20V 3.5A TO236AB

Detailed Description P-Channel 20 V 3.5A (Ta) 510mW (Ta), 4.15W (Tc) S

urface Mount TO-236AB



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMV48XPAR	Nexperia USA Inc.
Series:	Product Status:
	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	3.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
2.5V, 4.5V	55mOhm @ 2.4A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
1.25V @ 250μA	11 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±12V	1000 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	510mW (Ta), 4.15W (Tc)
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Supplier Device Package:	Package / Case:
TO-236AB	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
PMV48	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



PMV48XPA

20 V, P-channel Trench MOSFET

10 March 2014

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Very fast switching
- AEC-Q101 qualified

3. Applications

- High-side loadswitch
- · High-speed line driver
- Relay driver
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-3.5	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.4 A; T_j = 25 °C		-	48	55	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1 2	G V
			TO-236AB (SOT23)	S
				017aaa094

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage				
	Name	Description	Version			
PMV48XPA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV48XPA	%DZ

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-3.5	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.2	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-14	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW
			[1]	-	930	mW
		T _{sp} = 25 °C		-	4150	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode		'		'	,
Is	source current	T _{amb} = 25 °C	[1]	-	-1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

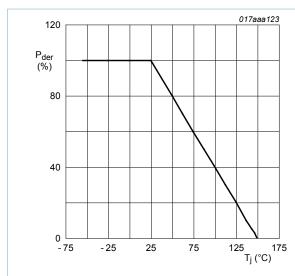


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

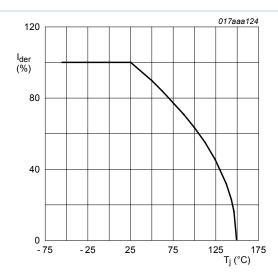


Fig. 2. Normalized continuous drain current as a function of junction temperature

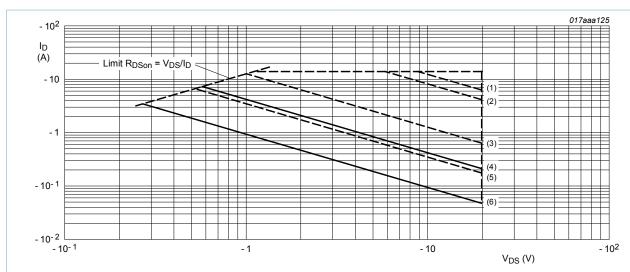
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

PMV48XPA

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I_{DM} = single pulse

(1) $t_p = 100 \mu s$

(2) $t_p = 1 \text{ ms}$

 $(3) t_p = 10 \text{ ms}$

(4) DC; T_{sp} = 25 °C

 $(5) t_p = 100 \text{ ms}$

(6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 6 cm²

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	213	245	K/W
			[2]	-	117	135	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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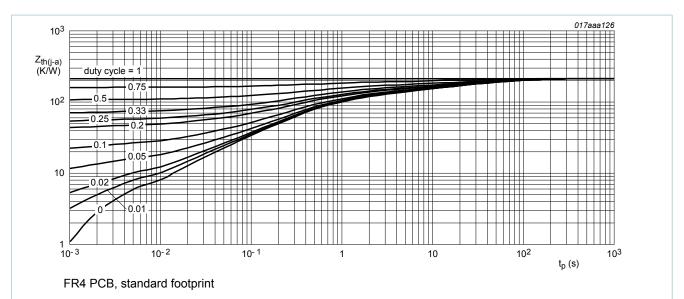


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

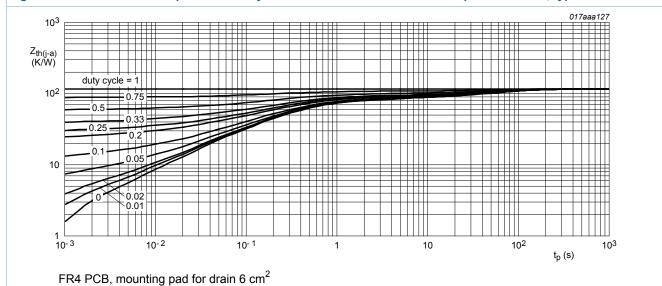


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _{amb} = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -2.4 A; T_j = 25 °C	-	48	55	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -2.4 A; T _j = 150 °C	-	70	80	mΩ
		V _{GS} = -2.5 V; I _D = -2 A; T _j = 25 °C	-	71	81	mΩ
9 _{fs}	forward transconductance	V_{DS} = -12 V; I_{D} = -2 A; T_{j} = 25 °C	-	12	-	S
Dynamic ch	naracteristics		'			
Q _{G(tot)}	total gate charge	V _{DS} = -10 V; I _D = -1 A; V _{GS} = -4.5 V;	-	8.5	11	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1.8	-	nC
Q_{GD}	gate-drain charge		-	1.8	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	1000	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	130	-	pF
C _{rss}	reverse transfer capacitance		-	90	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -1 A; V_{GS} = -4.5 V;	-	11	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 ^{\circ}C$	-	13	-	ns
t _{d(off)}	turn-off delay time		-	61	-	ns
t _f	fall time		-	23	-	ns
Source-drai	in diode			1	1	
V _{SD}	source-drain voltage	I _S = -2.4 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.82	-1.2	V

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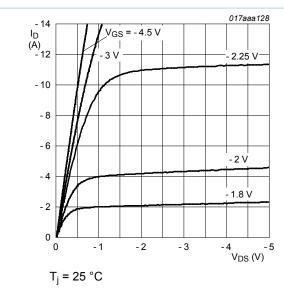
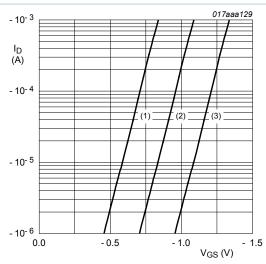


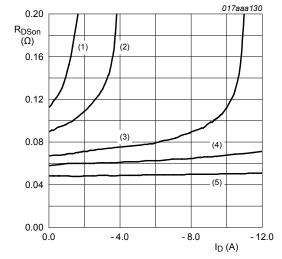
Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i = 25 \,^{\circ}C; \, V_{DS} = -3 \,^{\circ}V$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



$$T_i = 25 \,^{\circ}C$$

$$(1) V_{GS} = -1.8 V$$

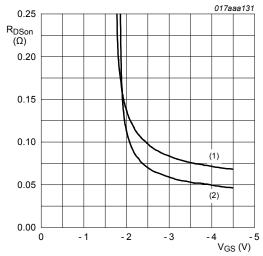
(2)
$$V_{GS} = -2.0 \text{ V}$$

$$(3) V_{GS} = -2.25 V$$

$$(4) V_{GS} = -3.0 V$$

$$(5) V_{GS} = -4.5 V$$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



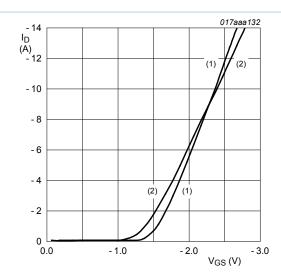
$$I_D = -2.4 A$$

(1)
$$T_i = 125 \, ^{\circ}C$$

(2)
$$T_i = 25 \, ^{\circ}C$$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$

(1) $T_j = 25$ °C

(2) $T_j = 150 \, ^{\circ}C$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

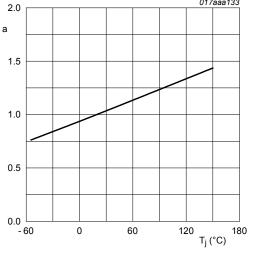
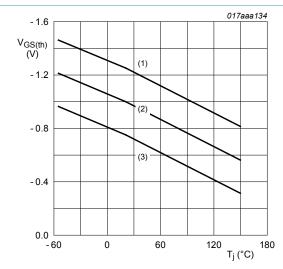


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

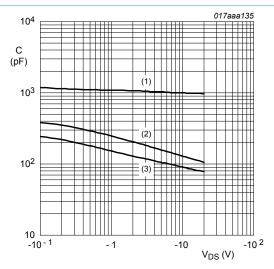
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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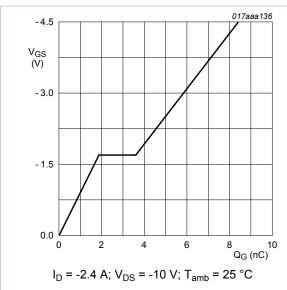


Fig. 14. Gate-source voltage as a function of gate charge; typical values

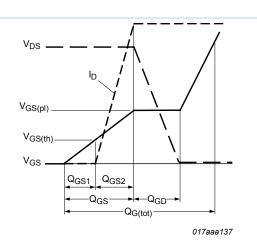
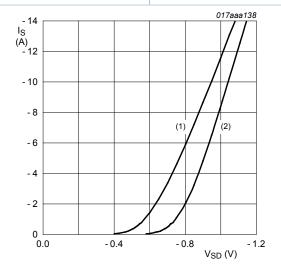


Fig. 15. Gate charge waveform definitions



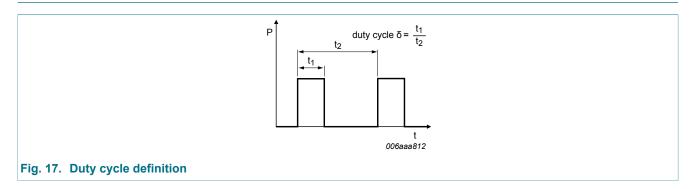
 $V_{GS} = 0 V$ (1) $T_j = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 16. Source current as a function of source-drain voltage; typical values

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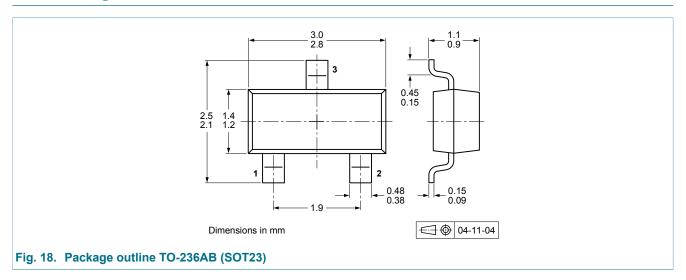
11. Test information



11.1 Quality information

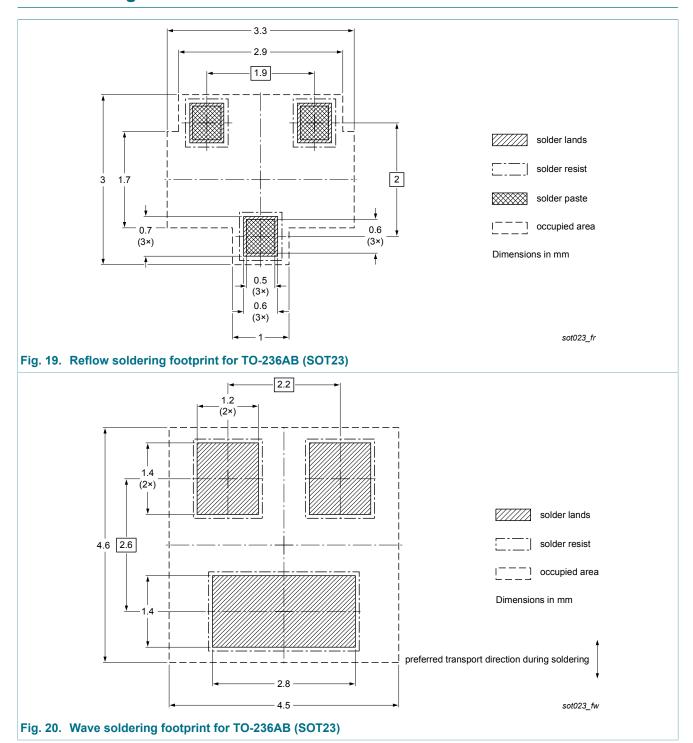
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV48XPA v.1	20140310	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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